

F. Silicon and Group-IV Devices and Integration Technology 분과

2020년 2월 13일(목), 09:00-10:30 / Room B (에메랄드 II+III, 5층)

■ [TB1-F] Emerging Device Technology I

좌장: 김상완 교수 (아주대학교), 권대웅 교수 (인하대학교)

TB1-F-1 09:00-09:30	[초청] Optimization of Spacer and Source/Channel Junction to Improve TFET Characteristics Garam Kim ¹ and Sangwan Kim ² <i>¹Myongji University, ²Ajou University</i>
TB1-F-2 09:30-09:45	Switching Characteristics Analysis of Tunnel Field-effect Transistor with Elevated Drain by Changing Drain Underlap Length Changha Kim ¹ , Kitae Lee ¹ , Junil Lee ¹ , Ryoongbin Lee ¹ , Sihyun Kim ¹ , Hyun-min Kim ¹ , Sangwan Kim ² and Byung-Gook Park ¹ <i>¹Inter-University Semiconductor Research Center (ISRC) and Department of Electrical and Computer Engineering, Seoul National University, ²Department of Electrical and Computer Engineering, Ajou University</i>
TB1-F-3 09:45-10:00	Digital Inverter with Positive Feedback Field Effect Transistor Changhoon Lee and Changhwan Shin <i>Department of Electrical and Computer Engineering, Sungkyunkwan University</i>
TB1-F-4 10:00-10:15	A Novel Gate-normal Hetero-gate-dielectric (GHG) Tunnel Field-effect Transistors (TFETs) Jang Woo Lee and Woo Young Choi <i>Department of Electronic Engineering, Sogang University</i>
TB1-F-5 10:15-10:30	Capacitorless Double-Gate PNP TFET 1T DRAM with SiGe Channel Jae Seung Woo and Woo Young Choi <i>Department of Electronic Engineering, Sogang University</i>